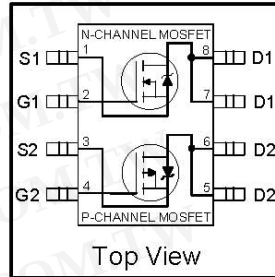


IRF7309PbF

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

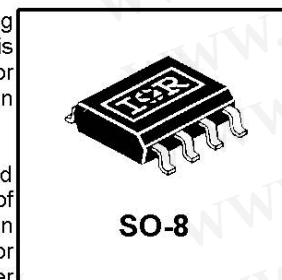


	N-Ch	P-Ch
V_{DS}	30V	-30V
$R_{DS(on)}$	0.050Ω	0.10Ω

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design for which HEXFET Power MOSFETs are well known, provides the designer with an extremely efficient device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra-red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Absolute Maximum Ratings

Parameter		Max.		Units
		N-Channel	P-Channel	
I_D @ $T_A = 25^\circ\text{C}$	10 Sec. Pulse Drain Current, V_{GS} @ 10V	4.7	-3.5	A
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	4.0	-3.0	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.2	-2.4	A
I_{DM}	Pulsed Drain Current Φ	16	-12	A
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount)**	1.4		W
	Linear Derating Factor (PCB Mount)**	0.011		W/°C
V_{GS}	Gate-to-Source Voltage	± 20		V
dv/dt	Peak Diode Recovery dv/dt Φ	6.9	-6.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units
$R_{\theta JA}$	—	—	90	°C/W

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	N-Ch 30 P-Ch -30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$ $V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	N-Ch — P-Ch —	0.032 0.037	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(ON)}$	N-Ch — P-Ch —	0.050 0.080 0.10 0.16	—	Ω	$V_{GS} = 10V, I_D = 2.4A$ ③ $V_{GS} = 4.5V, I_D = 2.0A$ ③ $V_{GS} = -10V, I_D = -1.8A$ ③ $V_{GS} = -4.5V, I_D = -1.5A$ ③
$V_{GS(th)}$	N-Ch 1.0 P-Ch -1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$ $V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	N-Ch 5.2 P-Ch 2.5	—	—	S	$V_{DS} = 15V, I_D = 2.4A$ ③ $V_{DS} = -24V, I_D = -1.8A$ ③
I_{DSS}	N-Ch — P-Ch —	—	1.0 -1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$ $V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	N-P —	—	±100	nA	$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ $V_{GS} = \pm 20V$
Q_g	N-Ch — P-Ch —	—	25 25	nC	N-Channel $I_D = 2.6A, V_{DS} = 16V, V_{GS} = 4.5V$ ③
Q_{gs}	N-Ch — P-Ch —	—	2.9 2.9	nC	P-Channel $I_D = -2.2A, V_{DS} = -16V, V_{GS} = -4.5V$
Q_{gd}	N-Ch — P-Ch —	—	7.9 9.0	nC	
$t_{d(on)}$	N-Ch — P-Ch —	6.8 11	—	ns	N-Channel $V_{DD} = 10V, I_D = 2.6A, R_G = 6.0\Omega, R_D = 3.8\Omega$ ③
t_r	N-Ch — P-Ch —	21 17	—	ns	
$t_{d(off)}$	N-Ch — P-Ch —	22 25	—	ns	P-Channel $V_{DD} = -10V, I_D = -2.2A, R_G = 6.0\Omega, R_D = 4.5\Omega$
t_f	N-Ch — P-Ch —	7.7 18	—	ns	
L_D	N-P —	4.0	—	nH	Between lead tip and center of die contact
L_S	N-P —	6.0	—	nH	
C_{iss}	N-Ch — P-Ch —	520 440	—	pF	N-Channel $V_{GS} = 0V, V_{DS} = 15V, f = 1.0\text{MHz}$ ③
C_{oss}	N-Ch — P-Ch —	180 200	—	pF	P-Channel $V_{GS} = 0V, V_{DS} = -15V, f = 1.0\text{MHz}$
C_{rss}	N-Ch — P-Ch —	72 93	—	pF	

Source-Drain Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	N-Ch — P-Ch —	—	1.8 -1.8	A	
I_{SM}	N-Ch — P-Ch —	—	16 -12	A	
V_{SD}	N-Ch — P-Ch —	—	1.0 -1.0	V	$T_J = 25^\circ\text{C}, I_S = 1.8A, V_{GS} = 0V$ ③ $T_J = 25^\circ\text{C}, I_S = -1.8A, V_{GS} = 0V$ ③
t_{rr}	N-Ch — P-Ch —	47 53	71 80	ns	N-Channel $T_J = 25^\circ\text{C}, I_F = 2.6A, di/dt = 100A/\mu s$
Q_{rr}	N-Ch — P-Ch —	56 66	84 99	nC	P-Channel $T_J = 25^\circ\text{C}, I_F = -2.2A, di/dt = 100A/\mu s$ ③
t_{on}	N-P —	—	—	—	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 23)

② N-Channel $I_{SD} \leq 2.4A, di/dt \leq 73A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

P-Channel $I_{SD} \leq -1.8A, di/dt \leq 90A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

N-Channel

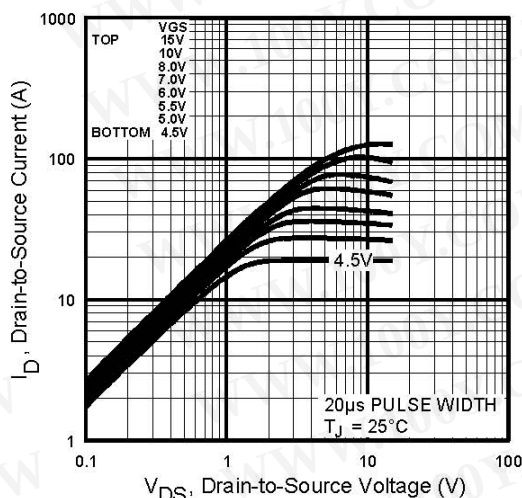


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ\text{C}$

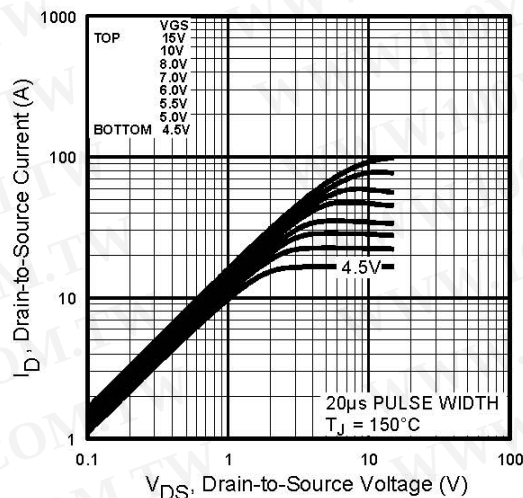


Fig 2. Typical Output Characteristics,
 $T_J = 150^\circ\text{C}$

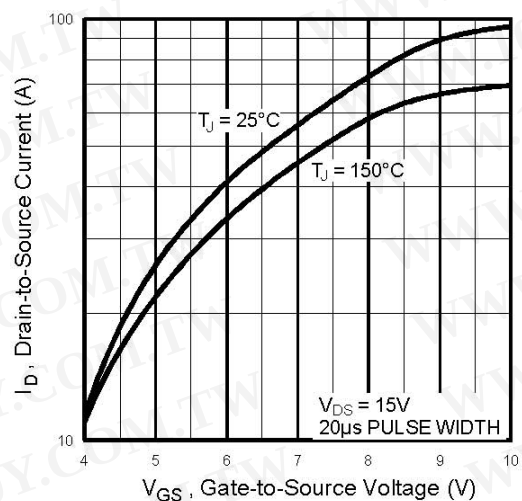


Fig 3. Typical Transfer Characteristics

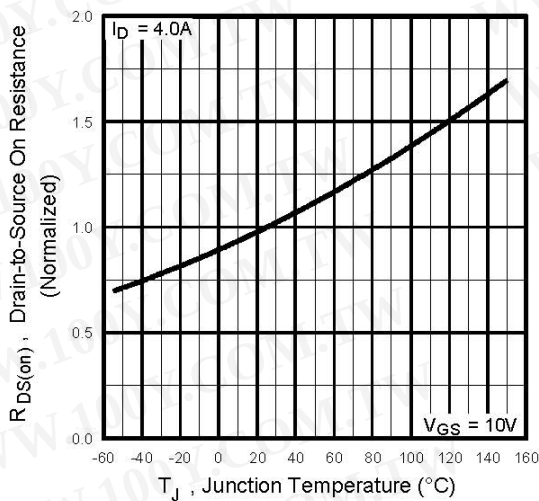


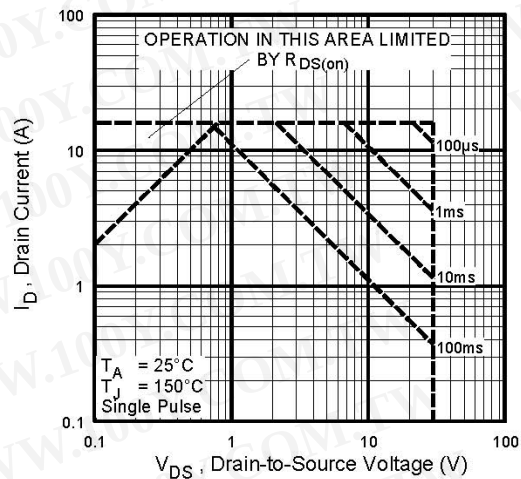
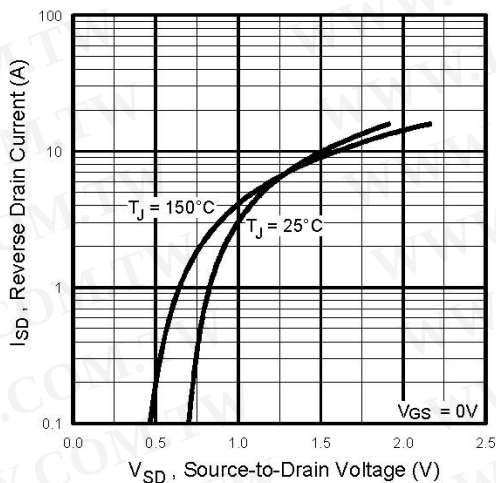
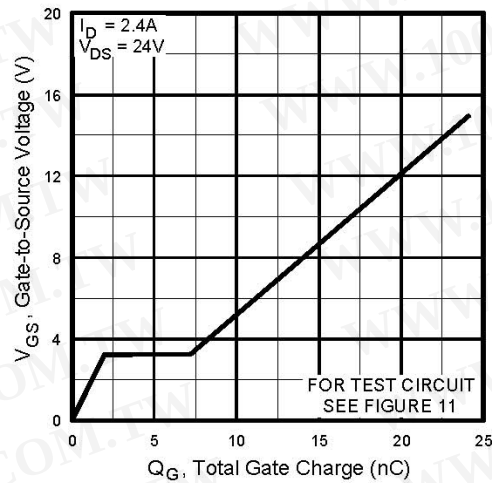
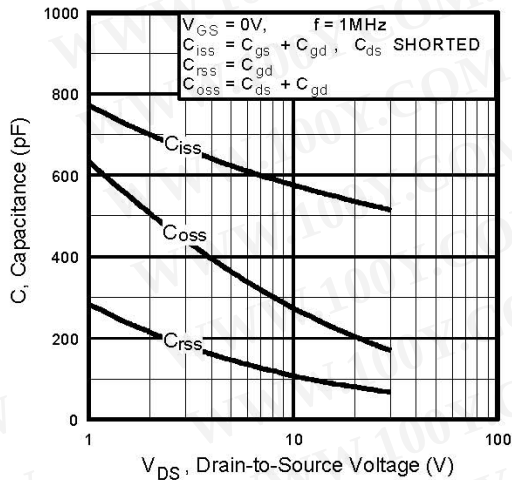
Fig 4. Normalized On-Resistance
Vs. Temperature

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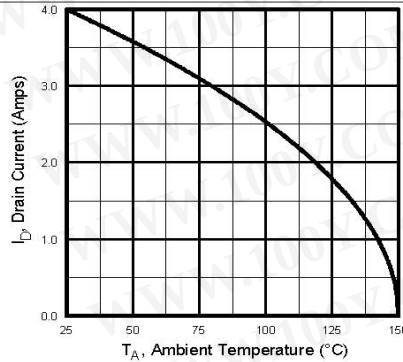


Fig 9. Max. Drain Current Vs. Ambient Temp.

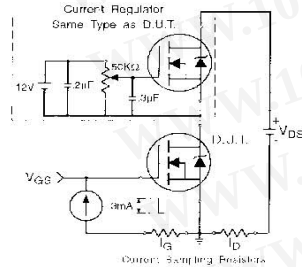


Fig 11a. Gate Charge Test Circuit

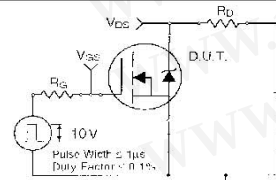


Fig 10a. Switching Time Test Circuit

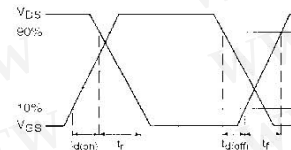


Fig 10b. Switching Time Waveforms

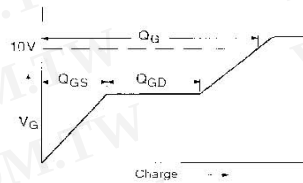


Fig 11b. Basic Gate Charge Waveform

P-Channel

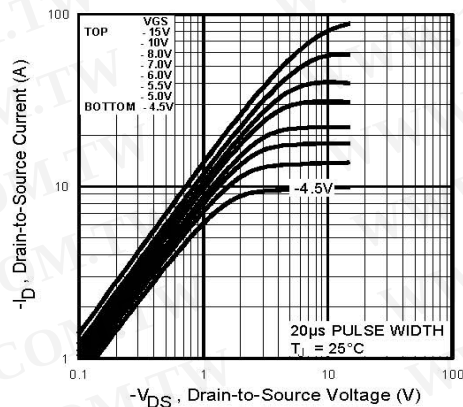


Fig 12. Typical Output Characteristics, $T_J = 25^\circ\text{C}$

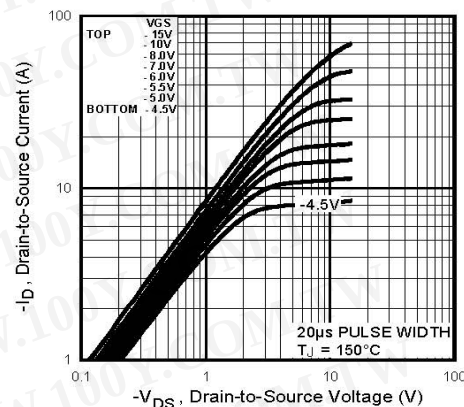


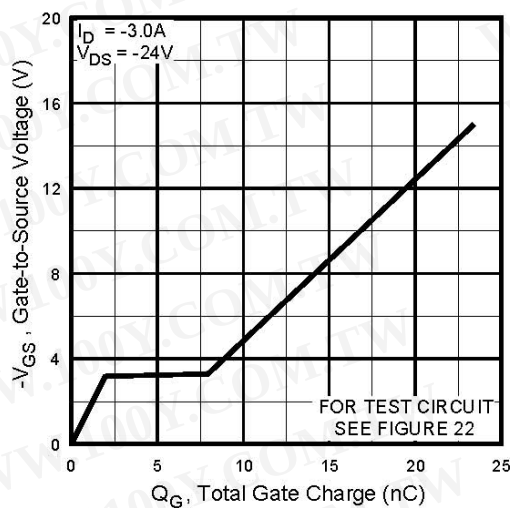
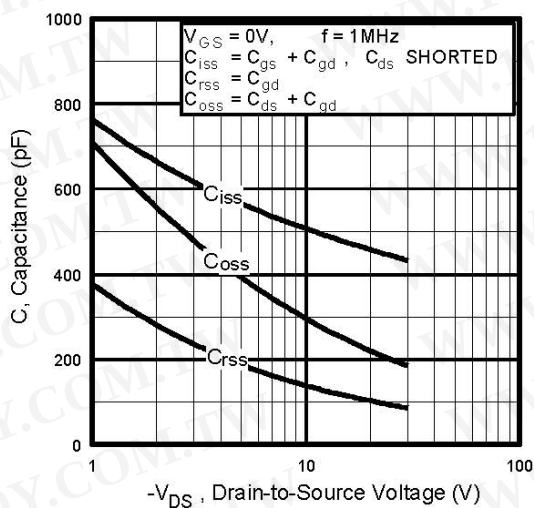
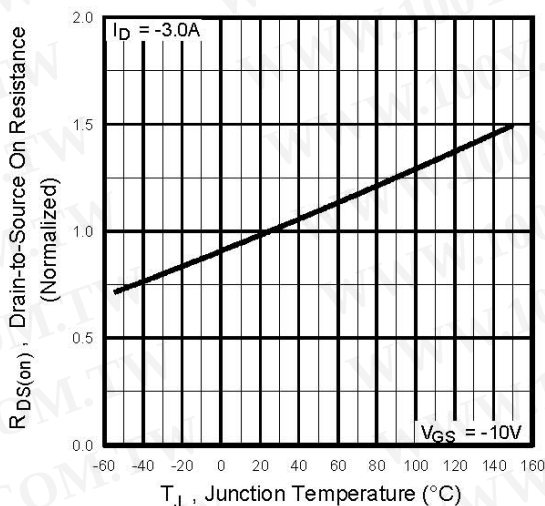
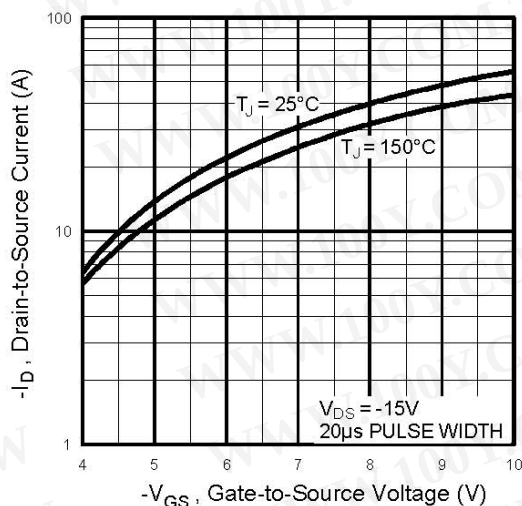
Fig 13. Typical Output Characteristics, $T_J = 150^\circ\text{C}$

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P-Channel



P-Channel

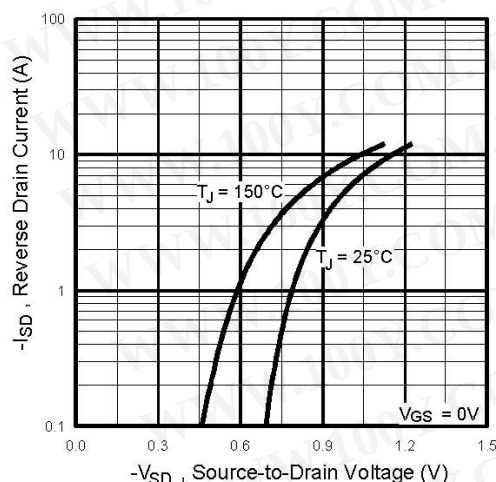


Fig 18. Typical Source-Drain Diode Forward Voltage

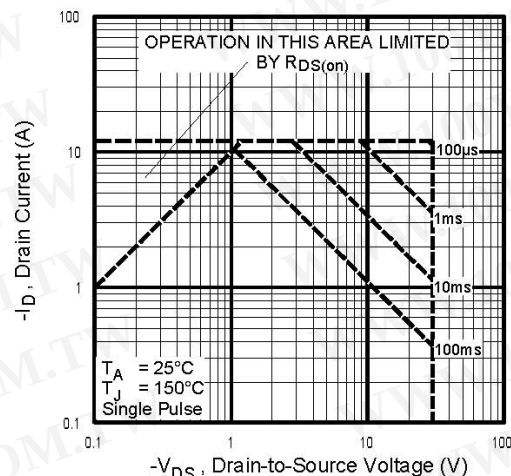


Fig 19. Maximum Safe Operating Area

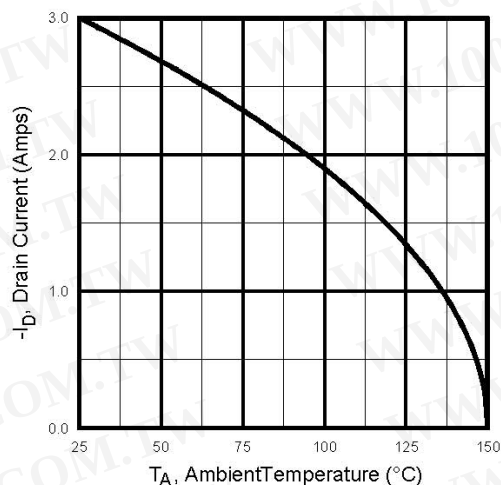


Fig 20. Max. Drain Current Vs. Ambient Temp.

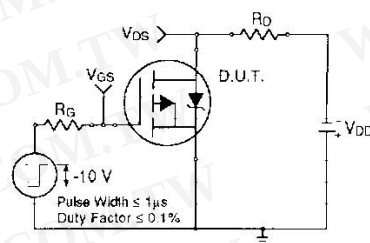


Fig 21a. Switching Time Test Circuit

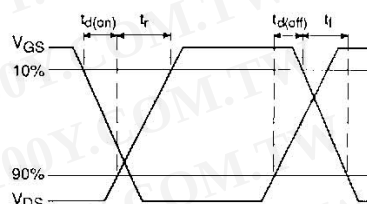


Fig 21b. Switching Time Waveforms

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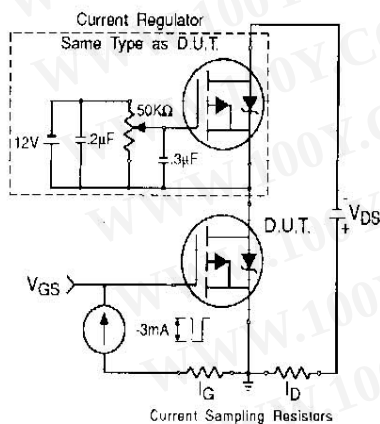


Fig 22b. Gate Charge Test Circuit

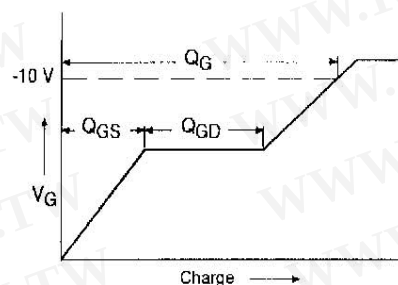


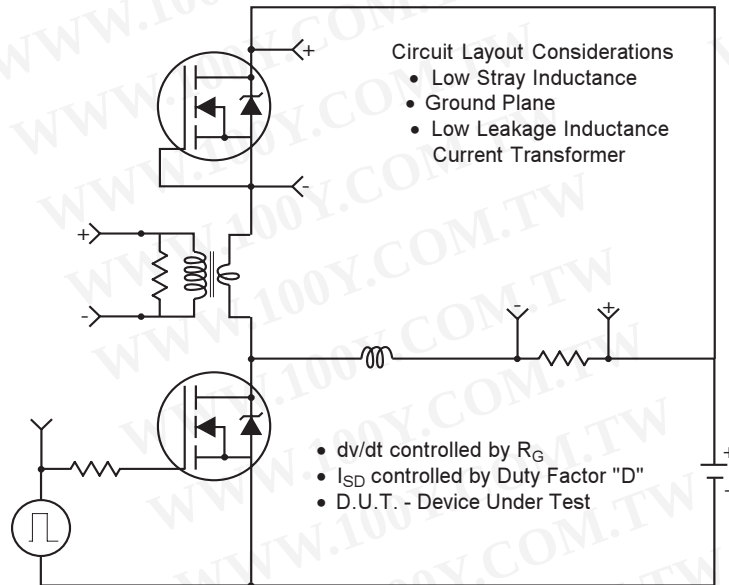
Fig 22b. Basic Gate Charge Waveform

N- and P-Channel



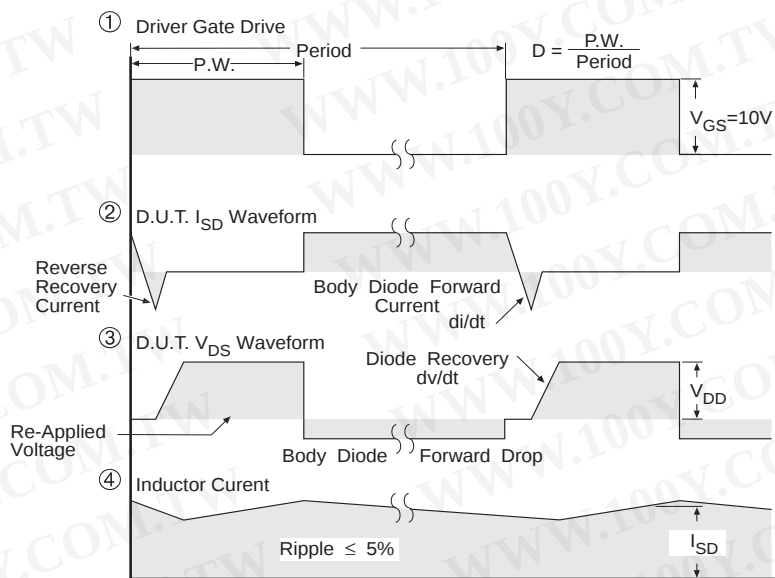
Fig 23. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements



*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 24. For N and P Channel HEXFETS

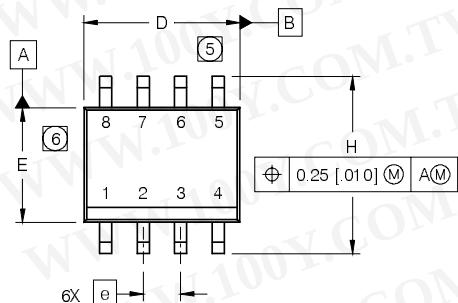
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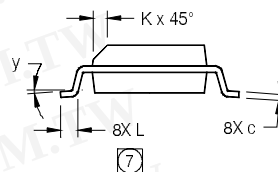
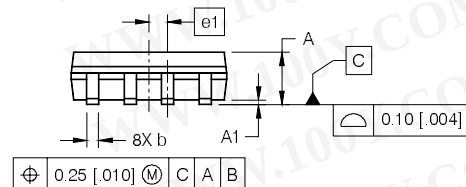
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SO-8 Package Details

Dimensions are shown in millimeters (inches)



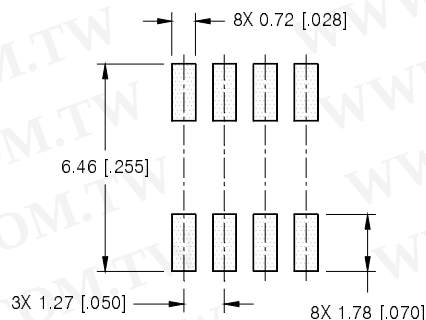
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

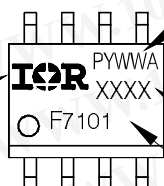
FOOTPRINT



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

INTERNATIONAL
 RECTIFIER
 LOGO



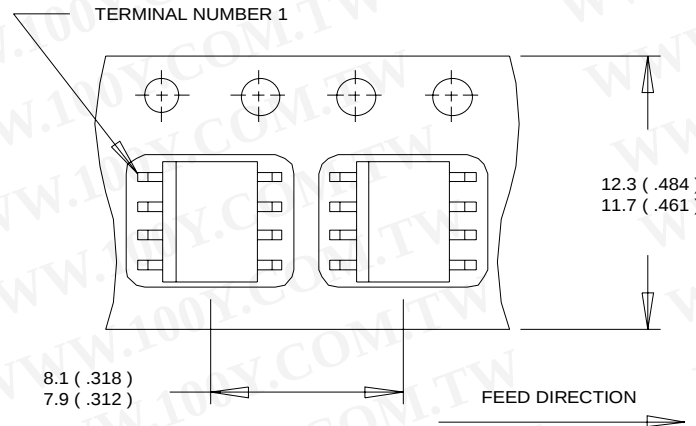
DATE CODE (YWW)
 P = DESIGNATES LEAD-FREE
 PRODUCT (OPTIONAL)
 Y = LAST DIGIT OF THE YEAR
 WW = WEEK
 A = ASSEMBLY SITE CODE
 LOT CODE
 PART NUMBER

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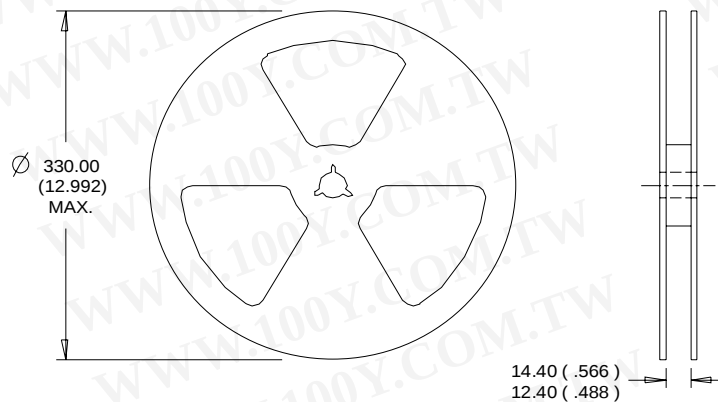
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SO-8 Tape and Reel



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

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TAC Fax: (310) 252-7903

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